

## Abstract

Integrated circuit arrangement with capacitor and fabrication method

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An explanation is given, inter alia, of an integrated circuit arrangement (120), which contains a transistor (122), preferably a so-called FinFET, and a capacitor (124). The bottom electrode of the capacitor (124) is  
10 arranged together with a channel region of the transistor (122) in an SOI substrate. The circuit arrangement (120) is simple to fabricate and has outstanding electronic properties.

15 (figure 17)